L Number	Hits	Search Text	DB	Time stamp
1	1	((esd or (electrostatic adj discharge))	USPAT;	2003/08/21 14:30
		adj protection) and (anti adj punch adj	US-PGPUB;	
		through adj structures)	EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0000/00/01 14/00
2	3		USPAT;	2003/08/21 14:23
		adj protection) and (anti adj punch adj	US-PGPUB; EPO; JPO;	
		through)	DERWENT;	
			IBM TDB	
3	167	anti adj punch adj through	USPAT;	2003/08/21 14:24
		amor day panem day amaraya	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	2	anti adj punch adj through adj structure	USPAT;	2003/08/21 14:24
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
5	14	((esd or (electrostatic adj discharge))	USPAT;	2003/08/21 15:14
٦	14	adj protection) and (internal adj mos)	US-PGPUB;	2003/00/21 13.11
		adj proceedion, and (incernar adj mes)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
6	1	6008080.pn. and pocket	USPAT;	2003/08/21 15:52
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0000 (00 (01 15 50
7	2	6100141.pn. and internal	USPAT;	2003/08/21 15:52
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	2	((esd or (electrostatic adj discharge))	USPAT;	2003/08/21 09:40
	2	adj protection) and (active adj region)	US-PGPUB;	2000, 00, 21 03.10
		and (breakdown adj enhanced adj layer)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	387		USPAT;	2003/08/20 17:22
		adj protection) and (active adj region)	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
	1	((esd or (electrostatic adj discharge))	USPAT;	2003/08/20 17:23
_	1	adj protection) and (reduce adj breakdown	US-PGPUB;	2003/00/20 17:23
l i		adj voltage adj across adj doped adj	EPO; JPO;	
		drain)	DERWENT;	
			IBM_TDB	
-	1		USPĀT;	2003/08/20 17:24
		adj protection) and (reduce adj breakdown	US-PGPUB;	<b>.</b>
		adj voltage adj across adj drain)	EPO; JPO;	Ĭ
			DERWENT;	1
	4.1	(load on loloatrostationed: discharge)	IBM_TDB USPAT;	2003/08/20 17:32
-	41	((esd or (electrostatic adj discharge)) adj protection) and (reduce adj breakdown	USPAT; US-PGPUB;	2003/00/20 11:32
		adj protection; and (reduce adj breakdown adj voltage)	EPO; JPO;	
		aug voreuge,	DERWENT;	
			IBM TDB	
-	0	((esd or (electrostatic adj discharge))	USPAT;	2003/08/20 17:36
1		adj protection) and (first adj gate adj	US-PGPUB;	
1		oxide adj thickness)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/00/00 15 15
-	70		USPAT;	2003/08/20 17:41
		adj protection) and (thick adj gate adj	US-PGPUB;	
		oxide)	EPO; JPO; DERWENT;	
			IBM TDB	
Ll			1 2011 100	

		((esd or (electrostatic adj discharge))	USPAT;	2003/08/20 17:42
-	0	adj protection) and (multiple adj gate adj	US-PGPUB;	2003/00/20 17:42
		oxide adj thickness)	EPO; JPO;	
		Oxide adj thickness;	DERWENT;	
			IBM TDB	
	0	//and an (alestmentatic add discharge)	USPAT;	2003/08/20 17:42
_	U	, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	US-PGPUB;	2003/00/20 17.42
		adj protection) and (multiple adj gate adj	EPO; JPO;	
		oxide)	DERWENT;	
			IBM TDB	
		//	USPAT:	2003/08/21 08:43
-	13	((===================================	USPAT; US-PGPUB;	2003/08/21 08:43
		adj protection) and (different adj gate		
		adj oxide)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2002/08/21 00-44
-	1	5861345.pn. and (aspect adj ratio)	USPAT;	2003/08/21 08:44
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	, ,
-	0	5656337.pn. and (aspect adj ratio)	USPAT;	2003/08/21 08:44
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	6	(	USPAT;	2003/08/21 14:20
		adj protection) and (pocket adj	US-PGPUB;	
		implantations)	EPO; JPO;	
			DERWENT;	
			IBM TDB	1